

BGA715L7

Silicon Germanium GPS Low Noise Amplifier

Small Signal Discretes



Never stop thinking

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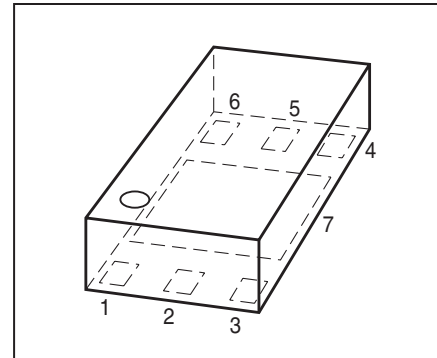
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1 Silicon Germanium GPS Low Noise Amplifier

Features

- High gain: 20 dB
- Low Noise Figure: 0.7 dB
- Low current consumption: 3.3 mA
- Supply voltage: 1.5 V to 3.3 V
- High input compression point -15.5 dBm at 1.8 V supply
- High input 3rd intercept point -7 dBm at 1.8 V supply
- B7HFM Silicon Germanium technology
- RF output internally matched to 50 Ω
- Low external part count
- 2kV HBM ESD protection (including AI-pin)
- Tiny TSLP-7-1 leadless package
- Moisture sensitivity level: MSL 1
- Pb-free (RoHS compliant) package



TSLP-7-1



Application

- 1575 MHz GPS, Galileo, GPS phone

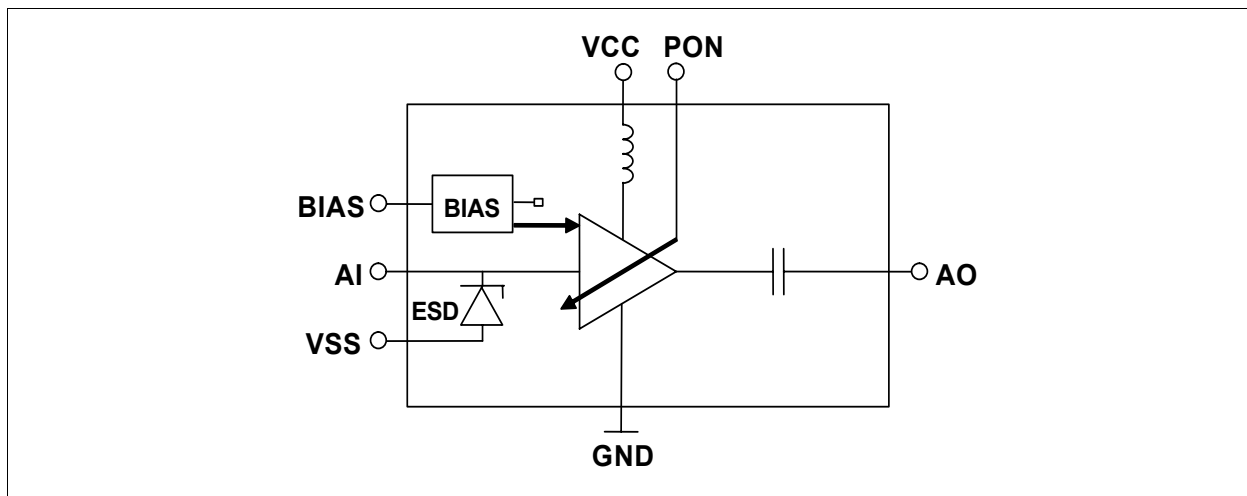


Figure 1 Blockdiagram

2 Description

The BGA715L7 is a front-end low noise amplifier for Global Positioning System (GPS) applications. The LNA provides 20 dB gain, 0.7 dB noise figure and high linearity performance in the application configuration described in [Chapter 4](#). Current consumption is as low as 3.3 mA. The BGA715L7 is based upon Infineon Technologies' B7HFM Silicon Germanium technology. It operates over a 1.5 V to 3.3 V supply range.

If an ultra low noise figure of 0.6 dB is required, please refer to Infineon BGA715L7 Application Note AN161.

| Type | Package | Marking |
|----------|----------|---------|
| BGA715L7 | TSLP-7-1 | UG |

Pin Definition and Function
Table 1 Pin Definition and Function

| Pin No. | Symbol | Function |
|---------|--------|------------------|
| 1 | AI | LNA input |
| 2 | BIAS | DC bias |
| 3 | GND | RF ground |
| 4 | PON | Power on control |
| 5 | VCC | DC supply |
| 6 | AO | LNA output |
| 7 | VSS | DC ground |

Maximum Ratings
Table 2 Maximum Ratings

| Parameter ¹⁾ | Symbol | Value | Unit |
|---|----------------|-------------------------|------|
| Voltage at pin VCC | V_{CC} | -0.3 ... 3.6 | V |
| Voltage at pin AI | V_{AI} | -0.3 ... 0.9 | V |
| Voltage at pin BIAS | V_{BIAS} | -0.3 ... 0.9 | V |
| Voltage at pin AO | V_{AO} | -0.3 ... $V_{CC} + 0.3$ | V |
| Voltage at pin PON | V_{PON} | -0.3 ... $V_{CC} + 0.3$ | V |
| Voltage at pin GND | V_{GND} | -0.3 ... 0.3 | V |
| Current into pin VCC | I_{CC} | 10 | mA |
| RF input power | P_{IN} | 10 | dBm |
| Total power dissipation | P_{tot} | 36 | mW |
| Junction temperature | T_J | 150 | °C |
| Ambient temperature range | T_A | -40 ... 85 | °C |
| Storage temperature range | T_{STG} | -65 ... 150 | °C |
| ²⁾ Human Body Model ESD capability, all pin to all pin | V_{ESD_HBM} | 2000 | V |
| ³⁾ Machine Model ESD capability, all pin to all pin | V_{ESD_MM} | 100 | V |

1) All voltages refer to VSS-Node.

2) According to JEDEC22A-114

3) According to JEDEC22A-115

Thermal resistance
Table 3 Thermal resistance

| Parameter | Symbol | Value | Unit |
|--|------------|-------|------|
| Junction - soldering point ¹⁾ | R_{thJS} | 159 | K/W |

1) For calculation of R_{thJA} please refer to Application Note Thermal Resistance

3 Electrical Characteristics

Table 4 Electrical Characteristics¹⁾: $T_A = 25\text{ °C}$, $V_{CC} = 1.8\text{ V}$, $V_{PON,ON} = 1.8\text{ V}$, $V_{PON,OFF} = 0\text{ V}$, $f = 1575\text{ MHz}$

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|----------------|--------|-------|----------|------|---|
| | | Min. | Typ. | Max. | | |
| Supply voltage | V_{CC} | 1.5 | 1.8 | 3.6 | V | |
| Supply current | I_{CC} | - | 3.3 | - | mA | ON-mode |
| | | - | 0.2 | 3 | μA | OFF-mode |
| Gain switch control voltage | V_{pon} | 1.0 | - | V_{CC} | V | ON-mode |
| | | 0 | - | 0.4 | V | OFF-mode |
| Gain switch control current | I_{pon} | - | 5 | - | μA | ON-mode |
| | | - | - | 1 | μA | OFF-mode |
| Power gain | $ S_{21} ^2$ | - | 20 | - | dB | High-gain Mode |
| Noise figure ²⁾ | NF | - | 0.7 | - | dB | $Z_S = 50\ \Omega$ |
| Input return loss | RL_{in} | - | 14 | - | dB | |
| Output return loss | RL_{out} | - | 13 | - | dB | |
| Reverse isolation | $1/ S_{12} ^2$ | - | 43 | - | dB | |
| Power gain settling time ³⁾ | t_S | - | 5 | - | μs | OFF- to ON-mode |
| | | - | 5 | - | μs | ON- to OFF-mode |
| Inband input 1dB compression point | IP_{1dB} | - | -15.5 | - | dBm | |
| Inband input 3rd order intercept point ⁴⁾ | IIP_3 | - | -7 | - | dBm | $f_1 = 1575\text{ MHz}$ $f_2 = f_1 +/ -1\text{ MHz}$ |
| Stability | k | - | > 1 | - | | $f = 20\text{ MHz} \dots 20\text{ GHz}$ |

1) Measured on BGA715L7 application board according to application schematic on page 7, including PCB losses (unless noted otherwise)

2) PCB transmission line- and connector losses of 0.05dB are subtracted

3) To be within 1 dB of the final gain OFF- to ON-mode; to be within 3 dB of the final gain ON- to OFF-mode

4) Input Power = -30 dBm for each tone

4 Application Information

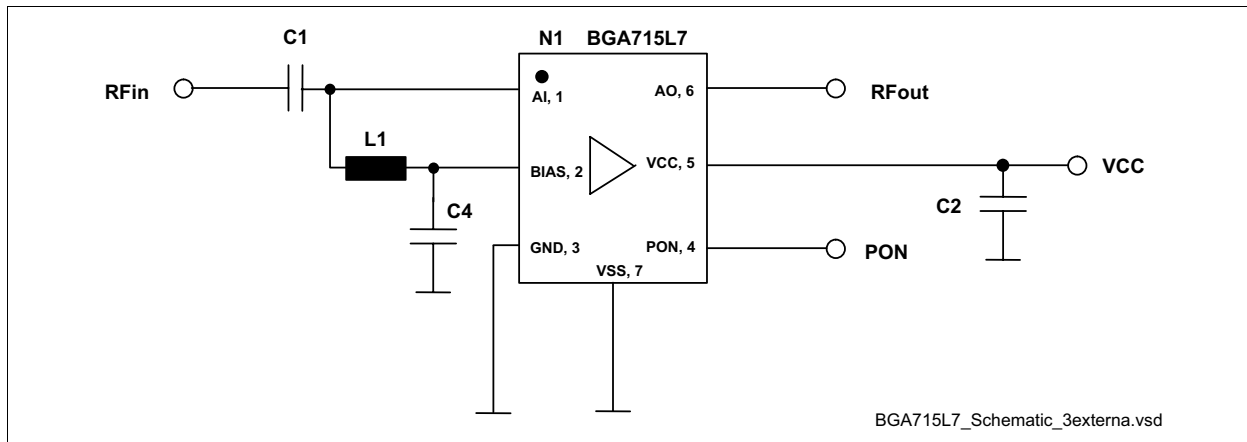


Figure 2 Application Schematic BGA715L7

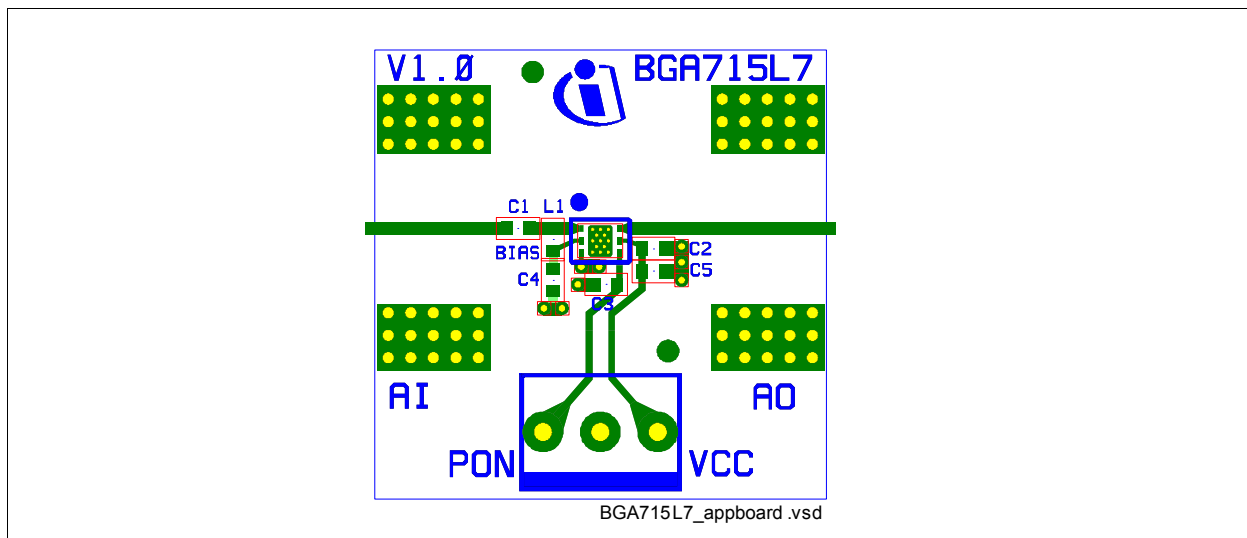


Figure 3 Application Board Drawing BGA715L7

Table 5 Bill of Materials

| Name | Value | Package | Manufacturer | Function |
|------|-------------------------|----------|--------------|--------------------------------|
| C1 | 1.8 pF | 0402 | Various | DC blocking and input matching |
| C2 | 1 μ F | 0402 | Various | RF block |
| C4 | 15 pF | 0402 | Various | RF block |
| L1 | 4.7 nH LQW15A series | 0402 | Murata | Bias feed and input matching |
| N1 | BGA715L7 | TSLP-7-1 | Infineon | SiGe LNA |

A list of all application notes is available at <http://goto.infineon.com/smallsignaldiscretes-appnotes>.

5 Package Information

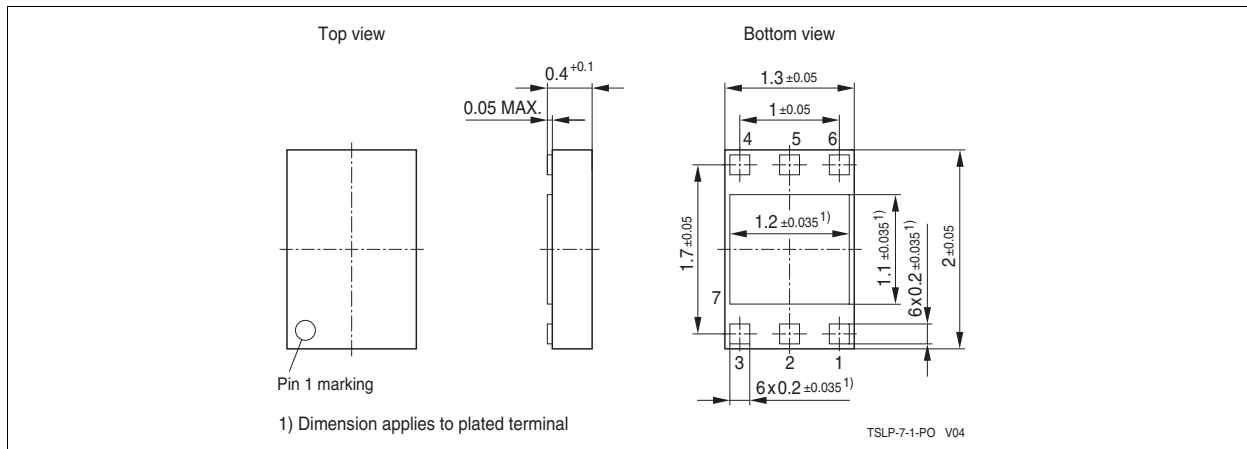


Figure 4 Package Dimensions for TSLP-7-1

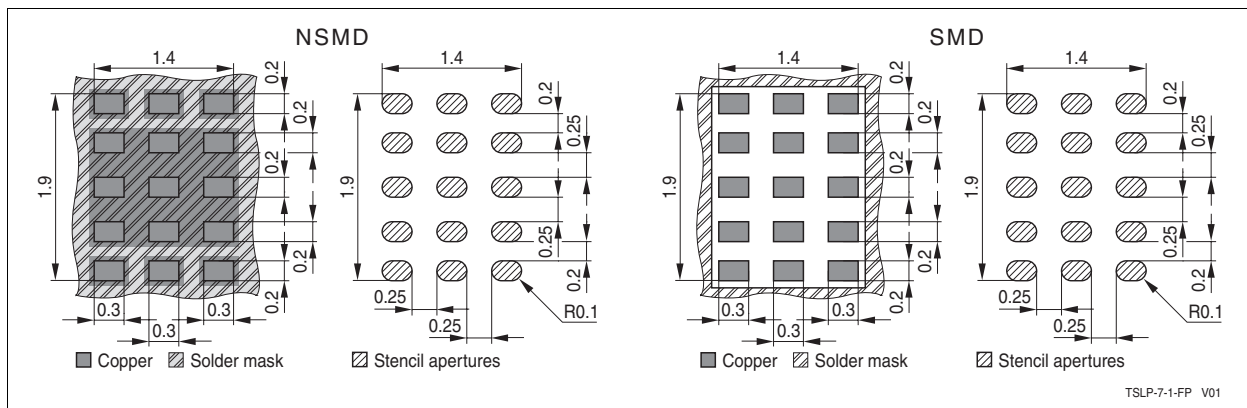


Figure 5 Footprint TSLP-7-1

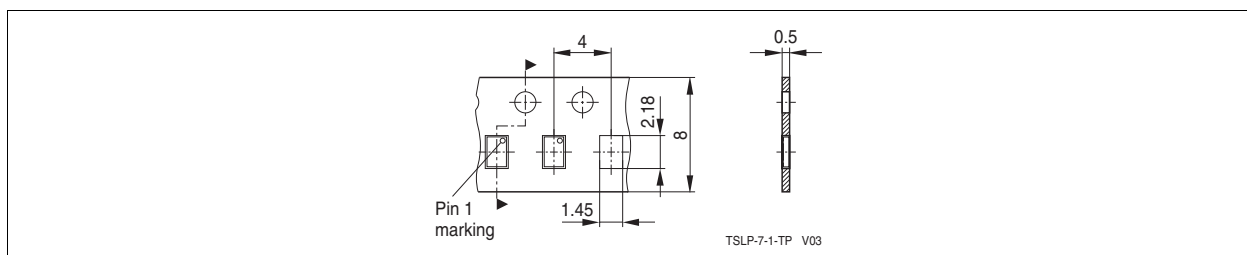


Figure 6 Tape & Reel Dimensions (Ø reel 180, pieces/reel 7500)